

Giuseppe Iannaccone

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

293
papers

8,099
citations

40
h-index

82
g-index

339
ext. papers

9,608
ext. citations

4
avg, IF

6.28
L-index

| # | Paper | IF | Citations |
|-----|--|------|-----------|
| 293 | Time domain analog neuromorphic engine based on high-density non-volatile memory in single-poly CMOS. <i>IEEE Access</i> , 2022 , 1-1 | 3.5 | 2 |
| 292 | A 0.6V $\bar{\bar{V}}$.8V Compact Temperature Sensor with 0.24 $^{\circ}$ C Resolution, $\bar{\bar{V}}$ 1.4 $^{\circ}$ C Inaccuracy and 1.06 nJ per Conversion. <i>IEEE Sensors Journal</i> , 2022 , 1-1 | 4 | 0 |
| 291 | Assessment of paper-based MoS2 FET for Physically Unclonable Functions. <i>Solid-State Electronics</i> , 2022 , 194, 108391 | 1.7 | 1 |
| 290 | Inkjet-printed low-dimensional materials-based complementary electronic circuits on paper. <i>Npj 2D Materials and Applications</i> , 2021 , 5, | 8.8 | 3 |
| 289 | . <i>IEEE Journal on Exploratory Solid-State Computational Devices and Circuits</i> , 2021 , 7, 141-149 | 2.4 | |
| 288 | Power Electronics Based on Wide-Bandgap Semiconductors: Opportunities and Challenges. <i>IEEE Access</i> , 2021 , 9, 139446-139456 | 3.5 | 5 |
| 287 | Ballistic two-dimensional lateral heterojunction bipolar transistor. <i>Physical Review Research</i> , 2021 , 3, | 3.9 | 1 |
| 286 | 1/f Noise Characterization of Bilayer MoS2 Field-Effect Transistors on Paper with Inkjet-Printed Contacts and hBN Dielectrics. <i>Advanced Electronic Materials</i> , 2021 , 7, 2100283 | 6.4 | 1 |
| 285 | Transport properties in partially overlapping van der Waals junctions through a multiscale investigation. <i>Physical Review B</i> , 2021 , 104, | 3.3 | 3 |
| 284 | Physical insights on transistors based on lateral heterostructures of monolayer and multilayer PtSe via Ab initio modelling of interfaces. <i>Scientific Reports</i> , 2021 , 11, 18482 | 4.9 | 1 |
| 283 | Single-poly floating-gate memory cell options for analog neural networks. <i>Solid-State Electronics</i> , 2021 , 185, 108062 | 1.7 | |
| 282 | Assessment of 2D-FET Based Digital and Analog Circuits on Paper. <i>Solid-State Electronics</i> , 2021 , 185, 108063 | 1.7 | 1 |
| 281 | Sub-Maxwellian Source Injection and Negative Differential Transconductance in Decorated Graphene Nanoribbons. <i>Physical Review Applied</i> , 2020 , 14, | 4.3 | 1 |
| 280 | Inkjet-printed graphene Hall mobility measurements and low-frequency noise characterization. <i>Nanoscale</i> , 2020 , 12, 6708-6716 | 7.7 | 8 |
| 279 | Lateral Heterostructure Field-Effect Transistors Based on Two-Dimensional Material Stacks with Varying Thickness and Energy Filtering Source. <i>ACS Nano</i> , 2020 , 14, 1982-1989 | 16.7 | 21 |
| 278 | Cold-source paradigm for steep-slope transistors based on van der Waals heterojunctions. <i>Physical Review Research</i> , 2020 , 2, | 3.9 | 3 |
| 277 | Stability and Startup of Non Linear Loop Circuits. <i>Lecture Notes in Electrical Engineering</i> , 2020 , 463-468 | 0.2 | |

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| 276 | Low-voltage 2D materials-based printed field-effect transistors for integrated digital and analog electronics on paper. <i>Nature Communications</i> , 2020 , 11, 3566 | 17.4 | 61 |
| 275 | Theoretical Analysis of a 2D Metallic/Semiconducting Transition-Metal Dichalcogenide NbS ₂ /WSe ₂ Hybrid Interface. <i>Advanced Theory and Simulations</i> , 2020 , 3, 2000164 | 3.5 | 1 |
| 274 | Analogue two-dimensional semiconductor electronics. <i>Nature Electronics</i> , 2020 , 3, 486-491 | 28.4 | 31 |
| 273 | . <i>IEEE Access</i> , 2020 , 8, 203525-203537 | 3.5 | 10 |
| 272 | Flexible One-Dimensional Metal/Insulator/Graphene Diode. <i>ACS Applied Electronic Materials</i> , 2019 , 1, 945-950 | 4 | 20 |
| 271 | A critical review of reduced one-dimensional beam models of piezoelectric composite beams. <i>Journal of Intelligent Material Systems and Structures</i> , 2019 , 30, 1148-1162 | 2.3 | 3 |
| 270 | Phonon-assisted carrier transport through a lattice-mismatched interface. <i>NPG Asia Materials</i> , 2019 , 11, | 10.3 | 4 |
| 269 | A Steep-Slope MoS ₂ -Nanoribbon MOSFET Based on an Intrinsic Cold-Contact Effect. <i>IEEE Electron Device Letters</i> , 2019 , 40, 1550-1553 | 4.4 | 15 |
| 268 | Ultralow Specific Contact Resistivity in Metal/Graphene Junctions via Contact Engineering. <i>Advanced Materials Interfaces</i> , 2019 , 6, 1801285 | 4.6 | 29 |
| 267 | All-2D Material Inkjet-Printed Capacitors: Toward Fully Printed Integrated Circuits. <i>ACS Nano</i> , 2019 , 13, 54-60 | 16.7 | 60 |
| 266 | Quantum engineering of transistors based on 2D materials heterostructures. <i>Nature Nanotechnology</i> , 2018 , 13, 183-191 | 28.7 | 198 |
| 265 | Reconfigurable Diodes Based on Vertical WSe Transistors with van der Waals Bonded Contacts. <i>Advanced Materials</i> , 2018 , 30, e1707200 | 24 | 21 |
| 264 | First-Principles Simulations of FETs Based on Two-Dimensional InSe. <i>IEEE Electron Device Letters</i> , 2018 , 39, 626-629 | 4.4 | 25 |
| 263 | The Role of Silicon Substrate on the Leakage Current Through GaN-on-Si Epitaxial Layers. <i>IEEE Transactions on Electron Devices</i> , 2018 , 65, 51-58 | 2.9 | 17 |
| 262 | A portable class of 3-transistor current references with low-power sub-0.5 V operation. <i>International Journal of Circuit Theory and Applications</i> , 2018 , 46, 779-795 | 2 | 7 |
| 261 | Modeling of Electron Devices Based on 2-D Materials. <i>IEEE Transactions on Electron Devices</i> , 2018 , 65, 4167-4179 | 2.9 | 16 |
| 260 | Variability-aware design of a bandgap voltage reference with 0.18% standard deviation and 68 nW power consumption. <i>International Journal of Circuit Theory and Applications</i> , 2018 , 46, 1985-1999 | 2 | 2 |
| 259 | Tunnel-Field-Effect Spin Filter from Two-Dimensional Antiferromagnetic Stanene. <i>Physical Review Applied</i> , 2018 , 10, | 4.3 | 6 |

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|-----|---|------|-----|
| 258 | Physical insights into the operation of a 1-nm gate length transistor based on MoS ₂ with metallic carbon nanotube gate. <i>Applied Physics Letters</i> , 2018 , 113, 183507 | 3-4 | 5 |
| 257 | Charge Injection in Normally-Off p-GaN Gate AlGaIn/GaN-on-Si HFETs 2018 , | | 5 |
| 256 | Stacking and interlayer electron transport in MoS ₂ . <i>Physical Review B</i> , 2018 , 98, | 3-3 | 9 |
| 255 | Threshold Voltage Instability in p-GaN Gate AlGaIn/GaN HFETs. <i>IEEE Transactions on Electron Devices</i> , 2018 , 65, 2454-2460 | 2-9 | 90 |
| 254 | An Ultralow-Voltage Energy-Efficient Level Shifter. <i>IEEE Transactions on Circuits and Systems II: Express Briefs</i> , 2017 , 64, 61-65 | 3-5 | 38 |
| 253 | High-Performance 2D p-Type Transistors Based on GaSe Layers: An Ab Initio Study. <i>Advanced Electronic Materials</i> , 2017 , 3, 1600399 | 6-4 | 18 |
| 252 | Water-based and biocompatible 2D crystal inks for all-inkjet-printed heterostructures. <i>Nature Nanotechnology</i> , 2017 , 12, 343-350 | 28-7 | 335 |
| 251 | Temperature Compensation of Silicon Lamina Resonators Using Etch Holes: Theory and Design Methodology. <i>IEEE Transactions on Ultrasonics, Ferroelectrics, and Frequency Control</i> , 2017 , 64, 879-887 | 3-2 | 3 |
| 250 | Growth-Induced Strain in Chemical Vapor Deposited Monolayer MoS ₂ : Experimental and Theoretical Investigation. <i>Advanced Materials Interfaces</i> , 2017 , 4, 1700031 | 4-6 | 35 |
| 249 | GaN Nanowire n-MOSFET With 5 nm Channel Length for Applications in Digital Electronics. <i>IEEE Electron Device Letters</i> , 2017 , 38, 859-862 | 4-4 | 33 |
| 248 | On current transients in MoS Field Effect Transistors. <i>Scientific Reports</i> , 2017 , 7, 11575 | 4-9 | 3 |
| 247 | Electrical properties of graphene-metal contacts. <i>Scientific Reports</i> , 2017 , 7, 5109 | 4-9 | 82 |
| 246 | High performance metal-insulator-graphene diodes for radio frequency power detection application. <i>Nanoscale</i> , 2017 , 9, 11944-11950 | 7-7 | 28 |
| 245 | A 220-mV input, 8.6 step-up voltage conversion ratio, 10.45-W output power, fully integrated switched-capacitor converter for energy harvesting 2017 , | | 6 |
| 244 | Attenuation limits in longitudinal phononic crystals. <i>Journal of Applied Physics</i> , 2017 , 122, 214502 | 2-5 | |
| 243 | Transistor Concepts Based on Lateral Heterostructures of Metallic and Semiconducting Phases of MoS ₂ . <i>Physical Review Applied</i> , 2017 , 8, | 4-3 | 24 |
| 242 | First principles investigation of tunnel FETs based on nanoribbons from topological two-dimensional materials. <i>Nanoscale</i> , 2017 , 9, 19390-19397 | 7-7 | 16 |
| 241 | Material-Device-Circuit Co-optimization of 2D Material based FETs for Ultra-Scaled Technology Nodes. <i>Scientific Reports</i> , 2017 , 7, 5016 | 4-9 | 13 |

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|-----|--|------|-----|
| 240 | Low energy/delay overhead level shifter for wide-range voltage conversion. <i>International Journal of Circuit Theory and Applications</i> , 2017 , 45, 1637-1646 | 2 | 3 |
| 239 | Insights on the physics and application of off-plane quantum transport through graphene and 2D materials. <i>Solid-State Electronics</i> , 2016 , 115, 213-218 | 1.7 | 10 |
| 238 | A Simple Method for the Design of 1-D MEMS Flexural Phononic Crystals. <i>IEEE Transactions on Electron Devices</i> , 2016 , 63, 4131-4137 | 2.9 | 3 |
| 237 | Performance of arsenene and antimonene double-gate MOSFETs from first principles. <i>Nature Communications</i> , 2016 , 7, 12585 | 17.4 | 224 |
| 236 | Comparison of short-channel effects in monolayer MoS2 based junctionless and inversion-mode field-effect transistors. <i>Applied Physics Letters</i> , 2016 , 108, 023506 | 3.4 | 13 |
| 235 | Two-dimensional transistors based on MoS2 lateral heterostructures 2016 , | | 1 |
| 234 | Gate-Tunable Atomically Thin Lateral MoS2 Schottky Junction Patterned by Electron Beam. <i>Nano Letters</i> , 2016 , 16, 3788-94 | 11.5 | 82 |
| 233 | . <i>IEEE Sensors Journal</i> , 2016 , 16, 5452-5462 | 4 | 127 |
| 232 | Suppressed and enhanced shot noise in one dimensional field-effect transistors. <i>Journal of Computational Electronics</i> , 2015 , 14, 94-106 | 1.8 | 3 |
| 231 | Characterization and modeling of CMOS-compatible acoustical particle velocity sensors for applications requiring low supply voltages. <i>Sensors and Actuators A: Physical</i> , 2015 , 229, 192-202 | 3.9 | 8 |
| 230 | Internet-of-things infrastructure as a platform for distributed measurement applications 2015 , | | 6 |
| 229 | . <i>IEEE Nanotechnology Magazine</i> , 2015 , 14, 1068-1082 | 2.6 | 23 |
| 228 | . <i>IEEE Transactions on Smart Grid</i> , 2015 , 6, 468-476 | 10.7 | 87 |
| 227 | Vertical transport in graphene-hexagonal boron nitride heterostructure devices. <i>Scientific Reports</i> , 2015 , 5, 14519 | 4.9 | 25 |
| 226 | A sub-1 V nanopower temperature-compensated sub-threshold CMOS voltage reference with 0.065%/V line sensitivity. <i>International Journal of Circuit Theory and Applications</i> , 2015 , 43, 421-426 | 2 | 4 |
| 225 | Relevance of the physics of off-plane transport through 2D materials on the design of vertical transistors 2015 , | | 2 |
| 224 | Understanding the nature of metal-graphene contacts: A theoretical and experimental study 2015 , | | 3 |
| 223 | Can graphene outperform indium tin oxide as transparent electrode in organic solar cells?. <i>2D Materials</i> , 2015 , 2, 045006 | 5.9 | 6 |

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|-----|--|------|------|
| 222 | A Sub- kT/q Voltage Reference Operating at 150 mV. <i>IEEE Transactions on Very Large Scale Integration (VLSI) Systems</i> , 2015 , 23, 1547-1551 | 2.6 | 39 |
| 221 | Graphene-based lateral heterostructure transistors exhibit better intrinsic performance than graphene-based vertical transistors as post-CMOS devices. <i>Scientific Reports</i> , 2014 , 4, 6607 | 4.9 | 24 |
| 220 | Heterojunction hybrid devices from vapor phase grown MoS ₂ . <i>Scientific Reports</i> , 2014 , 4, 5458 | 4.9 | 65 |
| 219 | Simulation of the Performance of Graphene FETs With a Semiclassical Model, Including Band-to-Band Tunneling. <i>IEEE Transactions on Electron Devices</i> , 2014 , 61, 1567-1574 | 2.9 | 12 |
| 218 | Bilayer Graphene Transistors for Analog Electronics. <i>IEEE Transactions on Electron Devices</i> , 2014 , 61, 729-733 | 3.3 | 31 |
| 217 | A picopower temperature-compensated, subthreshold CMOS voltage reference. <i>International Journal of Circuit Theory and Applications</i> , 2014 , 42, 1306-1318 | 2 | 14 |
| 216 | An Open-Source Multiscale Framework for the Simulation of Nanoscale Devices. <i>IEEE Transactions on Electron Devices</i> , 2014 , 61, 48-53 | 2.9 | 40 |
| 215 | On Transport in Vertical Graphene Heterostructures. <i>IEEE Electron Device Letters</i> , 2014 , 35, 966-968 | 4.4 | 10 |
| 214 | Electronics based on two-dimensional materials. <i>Nature Nanotechnology</i> , 2014 , 9, 768-79 | 28.7 | 1953 |
| 213 | Two-Dimensional Tunnel Transistors Based on Bi_2Se_3 Thin Film. <i>IEEE Electron Device Letters</i> , 2014 , 35, 129-131 | 4.4 | 23 |
| 212 | Optimization and benchmarking of graphene-based heterostructure FETs 2014 , | | 1 |
| 211 | Design of a 75-nW, 0.5-V subthreshold complementary metal-oxide-semiconductor operational amplifier. <i>International Journal of Circuit Theory and Applications</i> , 2014 , 42, 967-977 | 2 | 41 |
| 210 | Design of a nanopower current reference with reduced process variability. <i>Analog Integrated Circuits and Signal Processing</i> , 2013 , 77, 45-53 | 1.2 | 4 |
| 209 | 2013 , | | 18 |
| 208 | Implementation of nanoscale double-gate CMOS circuits using compact advanced transport models. <i>Microelectronics Journal</i> , 2013 , 44, 80-85 | 1.8 | 5 |
| 207 | Very Large Current Modulation in Vertical Heterostructure Graphene/hBN Transistors. <i>IEEE Transactions on Electron Devices</i> , 2013 , 60, 268-273 | 2.9 | 48 |
| 206 | An intragrid implementation embedded in an Internet of Things platform 2013 , | | 4 |
| 205 | Junction Engineering of 1T-DRAMs. <i>IEEE Electron Device Letters</i> , 2013 , 34, 408-410 | 4.4 | 24 |

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|-----|--|------|-----|
| 204 | Sensitivity-based investigation of threshold voltage variability in 32-nm flash memory cells and MOSFETs. <i>Solid-State Electronics</i> , 2013 , 84, 127-131 | 1.7 | 4 |
| 203 | Multiscale Modeling for Graphene-Based Nanoscale Transistors. <i>Proceedings of the IEEE</i> , 2013 , 101, 1653-1669 | 1.5 | 106 |
| 202 | Modeling of nanoscale devices with carriers obeying a three-dimensional density of states. <i>Journal of Applied Physics</i> , 2013 , 113, 143711 | 2.5 | 5 |
| 201 | Velocity saturation in few-layer MoS ₂ transistor. <i>Applied Physics Letters</i> , 2013 , 103, 233509 | 3.4 | 52 |
| 200 | Engineering Interband Tunneling in Nanowires With Diamond Cubic or Zincblende Crystalline Structure Based on Atomistic Modeling. <i>IEEE Nanotechnology Magazine</i> , 2013 , 12, 839-842 | 2.6 | 5 |
| 199 | Quantum transport modeling of defected graphene nanoribbons. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2012 , 44, 981-984 | 3 | 8 |
| 198 | Insights on radio frequency bilayer graphene FETs 2012 , | | 15 |
| 197 | Lateral graphene-hBCN heterostructures as a platform for fully two-dimensional transistors. <i>ACS Nano</i> , 2012 , 6, 2642-8 | 16.7 | 115 |
| 196 | Geometrical Effects on Valley-Orbital Filling Patterns in Silicon Quantum Dots for Robust Qubit Implementation. <i>Applied Physics Express</i> , 2012 , 5, 124001 | 2.4 | 16 |
| 195 | Two Dimensional Graphene/h-BCN Based Devices with Large Ion/Ioff Ratio for Digital Applications. <i>Advances in Science and Technology</i> , 2012 , 77, 266-269 | 0.1 | 1 |
| 194 | A Backscattering Model Incorporating the Effective Carrier Temperature in Nano-MOSFET. <i>IEEE Electron Device Letters</i> , 2011 , 32, 853-855 | 4.4 | 4 |
| 193 | . <i>IEEE Journal of Solid-State Circuits</i> , 2011 , 46, 465-474 | 5.5 | 164 |
| 192 | CMOS Silicon Physical Unclonable Functions Based on Intrinsic Process Variability. <i>IEEE Journal of Solid-State Circuits</i> , 2011 , 46, 1456-1463 | 5.5 | 43 |
| 191 | . <i>IEEE Transactions on Electron Devices</i> , 2011 , 58, 2824-2830 | 2.9 | 34 |
| 190 | . <i>IEEE Transactions on Electron Devices</i> , 2011 , 58, 691-697 | 2.9 | 8 |
| 189 | An Approach Based on Sensitivity Analysis for the Evaluation of Process Variability in Nanoscale MOSFETs. <i>IEEE Transactions on Electron Devices</i> , 2011 , 58, 2266-2273 | 2.9 | 4 |
| 188 | Nanodevices in Flatland: Two-dimensional graphene-based transistors with high Ion/Ioff ratio 2011 , | | 2 |
| 187 | Analytical drain current model reproducing advanced transport models in nanoscale double-gate (DG) MOSFETs 2011 , | | 1 |

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| 186 | Strong mobility degradation in ideal graphene nanoribbons due to phonon scattering. <i>Applied Physics Letters</i> , 2011 , 98, 212111 | 3.4 | 45 |
| 185 | Analytical drain current model reproducing advanced transport models in nanoscale cylindrical surrounding-gate (SRG) MOSFETs. <i>Journal of Applied Physics</i> , 2011 , 110, 034510 | 2.5 | 4 |
| 184 | Drift velocity peak and negative differential mobility in high field transport in graphene nanoribbons explained by numerical simulations. <i>Applied Physics Letters</i> , 2011 , 99, 242108 | 3.4 | 11 |
| 183 | Compact drain-current model for reproducing advanced transport models in nanoscale double-gate MOSFETs. <i>Semiconductor Science and Technology</i> , 2011 , 26, 095015 | 1.8 | 7 |
| 182 | Evaluation of threshold voltage dispersion in 45 nm CMOS technology with TCAD-based sensitivity analysis 2010 , | | 2 |
| 181 | Full band assessment of phonon-limited mobility in Graphene NanoRibbons 2010 , | | 2 |
| 180 | Simulation of hydrogenated graphene field-effect transistors through a multiscale approach. <i>Physical Review B</i> , 2010 , 82, | 3.3 | 43 |
| 179 | Multi-scale simulation of partially unzipped CNT hetero-junction Tunneling Field Effect Transistor 2010 , | | 4 |
| 178 | Atomistic quantum transport modeling of metal-graphene nanoribbon heterojunctions. <i>Physical Review B</i> , 2010 , 82, | 3.3 | 9 |
| 177 | Semi-analytical model for schottky-barrier carbon nanotube and graphene nanoribbon transistors 2010 , | | 3 |
| 176 | Effects due to backscattering and pseudogap features in graphene nanoribbons with single vacancies. <i>Physical Review B</i> , 2010 , 81, | 3.3 | 48 |
| 175 | Electric field control of spin rotation in bilayer graphene. <i>Nano Letters</i> , 2010 , 10, 4463-9 | 11.5 | 42 |
| 174 | Statistical theory of shot noise in quasi-one-dimensional field-effect transistors in the presence of electron-electron interaction. <i>Physical Review B</i> , 2010 , 81, | 3.3 | 9 |
| 173 | Enhanced shot noise in carbon nanotube FETs due to electron-hole interaction 2010 , | | 2 |
| 172 | Model of tunneling transistors based on graphene on SiC. <i>Applied Physics Letters</i> , 2010 , 96, 133508 | 3.4 | 25 |
| 171 | An energy case for hybrid datacenters. <i>Operating Systems Review (ACM)</i> , 2010 , 44, 76-80 | 0.8 | 65 |
| 170 | Analytical Model of One-Dimensional Carbon-Based Schottky-Barrier Transistors. <i>IEEE Transactions on Electron Devices</i> , 2010 , 57, 1616-1625 | 2.9 | 21 |
| 169 | . <i>IEEE Transactions on Electron Devices</i> , 2010 , 57, 1936-1941 | 2.9 | 19 |

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| 168 | Barrier Lowering and Backscattering Extraction in Short-Channel MOSFETs. <i>IEEE Transactions on Electron Devices</i> , 2010 , 57, 2132-2137 | 2.9 | 14 |
| 167 | Quantum analysis of shot noise suppression in a series of tunnel barriers. <i>Physical Review B</i> , 2009 , 79, | 3.3 | 11 |
| 166 | Time-dependent analysis of low VDD program operation in double-gate SONOS memories by full-band Monte Carlo simulation. <i>Journal of Applied Physics</i> , 2009 , 106, 104506 | 2.5 | |
| 165 | Analytical model for the 1/f noise in the tunneling current through metal-oxide-semiconductor structures. <i>Journal of Applied Physics</i> , 2009 , 106, 073710 | 2.5 | 21 |
| 164 | Enhanced shot noise in carbon nanotube field-effect transistors. <i>Applied Physics Letters</i> , 2009 , 95, 252108 | 3.4 | 2 |
| 163 | Analytical Model of Nanowire FETs in a Partially Ballistic or Dissipative Transport Regime. <i>IEEE Transactions on Electron Devices</i> , 2009 , | 2.9 | 6 |
| 162 | Shot Noise Suppression in Quasi-One-Dimensional Field-Effect Transistors. <i>IEEE Transactions on Electron Devices</i> , 2009 , 56, 2137-2143 | 2.9 | 17 |
| 161 | A Semianalytical Model of Bilayer-Graphene Field-Effect Transistor. <i>IEEE Transactions on Electron Devices</i> , 2009 , 56, 2979-2986 | 2.9 | 49 |
| 160 | A comparison of advanced transport models for the computation of the drain current in nanoscale nMOSFETs. <i>Solid-State Electronics</i> , 2009 , 53, 1293-1302 | 1.7 | 14 |
| 159 | A software platform for nanoscale device simulation and visualization 2009 , | | 1 |
| 158 | Comparison of advanced transport models for nanoscale nMOSFETs 2009 , | | 1 |
| 157 | Performance Analysis of Graphene Bilayer Transistors Through Tight-Binding Simulations 2009 , | | 9 |
| 156 | Analytical and TCAD-supported approach to evaluate intrinsic process variability in nanoscale MOSFETs 2009 , | | 2 |
| 155 | 2009 , | | 2 |
| 154 | Perspectives of graphene nanoelectronics: probing technological options with modeling 2009 , | | 20 |
| 153 | On the Possibility of Tunable-Gap Bilayer Graphene FET. <i>IEEE Electron Device Letters</i> , 2009 , 30, 261-264 | 4.4 | 74 |
| 152 | Numerical Analysis of Transport Properties of Boron-Doped Graphene FETs 2009 , | | 2 |
| 151 | 2009 , | | 5 |

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|-----|--|-----|-----|
| 150 | Ultralow-Voltage Bilayer Graphene Tunnel FET. <i>IEEE Electron Device Letters</i> , 2009 , 30, 1096-1098 | 4.4 | 114 |
| 149 | Corrections to a three-dimensional simulation study of the performance of carbon nanotube field-effect transistors with doped reservoirs and realistic geometry [Aug 06 1782-1788]. <i>IEEE Transactions on Electron Devices</i> , 2008 , 55, 1094-1095 | 2.9 | 3 |
| 148 | Performance Comparison of Graphene Nanoribbon FETs With Schottky Contacts and Doped Reservoirs. <i>IEEE Transactions on Electron Devices</i> , 2008 , 55, 2314-2323 | 2.9 | 108 |
| 147 | Shot noise in quasi one-dimensional FETs 2008 , | | 4 |
| 146 | Study of Warm-Electron Injection in Double-Gate SONOS by Full-Band Monte Carlo Simulation. <i>IEEE Electron Device Letters</i> , 2008 , 29, 1242-1244 | 4.4 | 5 |
| 145 | Modeling the gate current 1/f noise and its application to advanced CMOS devices 2008 , | | 1 |
| 144 | A model for MOS gate stack quality evaluation based on the gate current 1/f noise 2008 , | | 9 |
| 143 | CMOS unclonable system for secure authentication based on device variability 2008 , | | 20 |
| 142 | Hierarchical simulation of transport in silicon nanowire transistors. <i>Journal of Computational Electronics</i> , 2008 , 7, 415-418 | 1.8 | 4 |
| 141 | Low-voltage nanopower clock generator for RFID applications. <i>Microelectronics Journal</i> , 2008 , 39, 1736-1739 | 1.8 | 3 |
| 140 | Noise and reliability in simulated thin metal films. <i>Microelectronics Reliability</i> , 2008 , 48, 1015-1020 | 1.2 | 2 |
| 139 | Three-Dimensional Simulations of Quantum Confinement and Random Dopants Effects in Nanoscale nMOSFETs. <i>Journal of Computational and Theoretical Nanoscience</i> , 2008 , 5, 1115-1119 | 0.3 | 3 |
| 138 | Low voltage hot-carrier programming of ultra-scaled SOI finflash memories 2007 , | | 3 |
| 137 | Advantages of the FinFET architecture in SONOS and Nanocrystal memory devices 2007 , | | 13 |
| 136 | Equivalent resistance and noise of cascaded mesoscopic cavities. <i>International Journal of Circuit Theory and Applications</i> , 2007 , 35, 295-304 | 2 | 6 |
| 135 | Modeling of Tunnelling Currents in Hf-Based Gate Stacks as a Function of Temperature and Extraction of Material Parameters. <i>IEEE Transactions on Electron Devices</i> , 2007 , 54, 83-89 | 2.9 | 36 |
| 134 | Comparison of Modeling Approaches for the Capacitance-Voltage and Current-Voltage Characteristics of Advanced Gate Stacks. <i>IEEE Transactions on Electron Devices</i> , 2007 , 54, 106-114 | 2.9 | 25 |
| 133 | Direct Solution of the Boltzmann Transport Equation and Poisson-Schrödinger Equation for Nanoscale MOSFETs. <i>IEEE Transactions on Electron Devices</i> , 2007 , 54, 2901-2909 | 2.9 | 16 |

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|-----|--|-----|-----|
| 132 | 3D simulation of a silicon quantum dot in a magnetic field based on current spin density functional theory. <i>Journal of Computational Electronics</i> , 2007 , 6, 191-194 | 1.8 | 1 |
| 131 | A Voltage Regulator for Subthreshold Logic with Low Sensitivity to Temperature and Process Variations 2007 , | | 3 |
| 130 | A 109 nW, 44 ppm/°C CMOS Current Reference with Low Sensitivity to Process Variations 2007 , | | 14 |
| 129 | Probing Pauli blocking with shot noise in resonant tunneling diodes: Experiment and theory. <i>Physical Review B</i> , 2007 , 75, | 3.3 | 7 |
| 128 | Physical Model for NAND operation in SOI and Body-Tied Nanocrystal FinFLASH memories 2007 , | | 3 |
| 127 | . <i>IEEE Journal of Solid-State Circuits</i> , 2007 , 42, 1536-1542 | 5.5 | 161 |
| 126 | Simulation of Graphene Nanoribbon Field-Effect Transistors. <i>IEEE Electron Device Letters</i> , 2007 , 28, 760-762 | 4.4 | 249 |
| 125 | Coupled Mode Space Approach for the Simulation of Realistic Carbon Nanotube Field-Effect Transistors. <i>IEEE Nanotechnology Magazine</i> , 2007 , 6, 475-480 | 2.6 | 29 |
| 124 | Three-Dimensional Simulation of One-Dimensional Transport in Silicon Nanowire Transistors. <i>IEEE Nanotechnology Magazine</i> , 2007 , 6, 524-529 | 2.6 | 40 |
| 123 | Low-Voltage Low-Power CMOS Oscillator with Low Temperature and Process Sensitivity 2007 , | | 15 |
| 122 | Performance Comparison of Graphene Nanoribbon Schottky Barrier and MOS FETs 2007 , | | 5 |
| 121 | A Three-Dimensional Simulation Study of the Performance of Carbon Nanotube Field-Effect Transistors With Doped Reservoirs and Realistic Geometry. <i>IEEE Transactions on Electron Devices</i> , 2006 , 53, 1782-1788 | 2.9 | 75 |
| 120 | Time-Independent Simulation of QCA Circuits 2006 , 65-85 | | 2 |
| 119 | Analysis of shot noise suppression in mesoscopic cavities in a magnetic field. <i>Europhysics Letters</i> , 2006 , 73, 574-580 | 1.6 | 17 |
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